

RESEARCH OF THE MICRODEFECTS  
FORMATION PROCESS IN DISLOCATION-FREE  
SILICON MONOCRYSTALS OBTAINED  
BY THE CZOCHRALSKI METHOD

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S u m m a r y

With the help of transmission electron microscopy and optical microscopy, the researches of dislocation-free silicon monocrystals obtained by the Czochralski method are conducted. In the crystals which are grown with high growth rates, the joint existence of interstitial and vacancy microdefects is revealed.